

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

Case: SO-8

Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Terminal Connections: See Diagram Below

Marking Information: See Page 4

Ordering Information: See Page 4

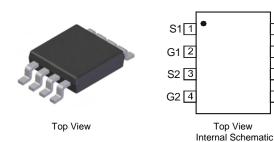
Weight: 0.072 grams (approximate)

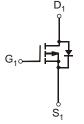
SO-8

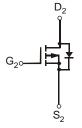
8 D1 7 D1 6 D2

5 D2

Top View







P-Channel MOSFET

P-Channel MOSFET

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 3) V _{GS} = -4.5V	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$	I _D	-4.6 -3	А
Pulsed Drain Current (Note 4)			I _{DM}	-20	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1.15	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{0JA}	109	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

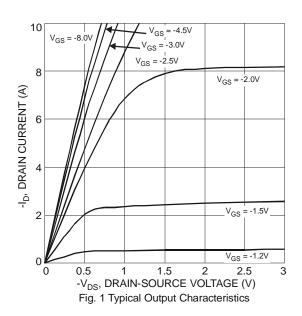


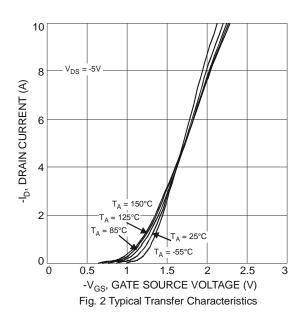
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)						_	
Gate Threshold Voltage	V _{GS(th)}	-0.45	-	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	55	75	$m\Omega$	$V_{GS} = -4.5V, I_D = -4.8A$	
	20 (011)	-	76	110		$V_{GS} = -2.5V, I_D = -1A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = -9V, I_{D} = -3.4A$	
Diode Forward Voltage	V_{SD}	-	-0.8	-1.2	V	$V_{GS} = 0V$, $I_S = -2A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss	-	608.4	-	pF	\	
Output Capacitance	Coss	-	81.5	-	pF	$V_{DS} = -6V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	72.4	-	pF		
Gate Resistance	Rg	-	44.91	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	-	6.5	-	nC	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_{D} = -3.2A$	
Gate-Source Charge	Q_{gs}	-	0.9	-	nC		
Gate-Drain Charge	Q_{gd}	-	1.5	-	nC		
Turn-On Delay Time	t _{D(on)}	-	12.45	-	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$ $R_{L} = 10\Omega, R_{G} = 1\Omega, I_{D} = -1A$	
Turn-On Rise Time	t _r	-	10.29	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	46.52	-	ns		
Turn-Off Fall Time	t _f	-	22.19	-	ns		

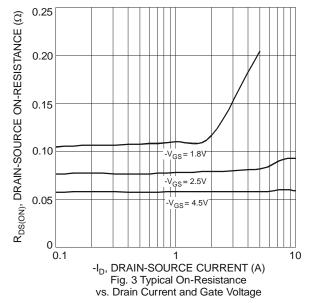
Notes:

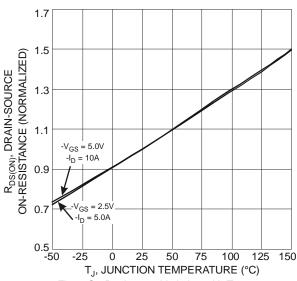
- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to production testing.

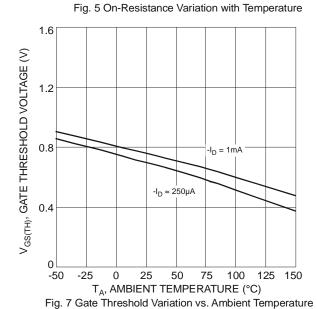












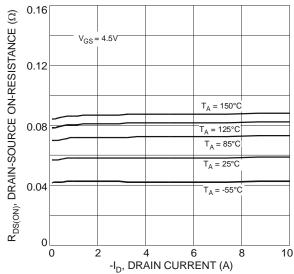


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

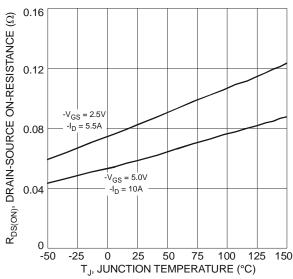


Fig. 6 On-Resistance Variation with Temperature

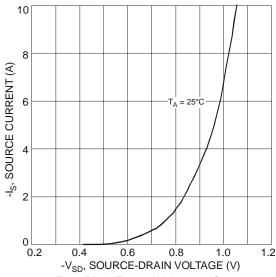
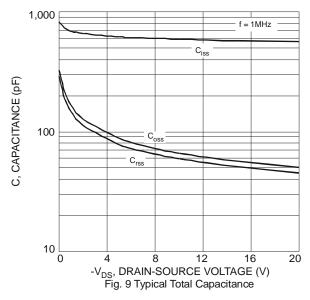


Fig. 8 Diode Forward Voltage vs. Current





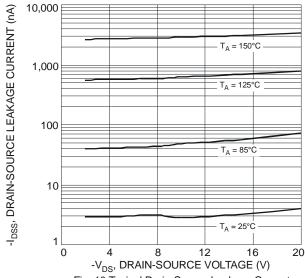
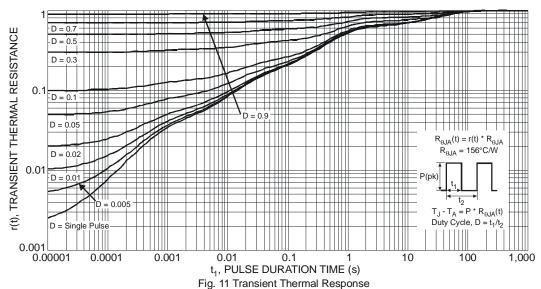


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

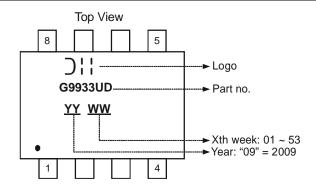


Ordering Information (Note 7)

Part Number	Case	Packaging	
DMG9933USD-13	SO-8	2500 / Tape & Reel	

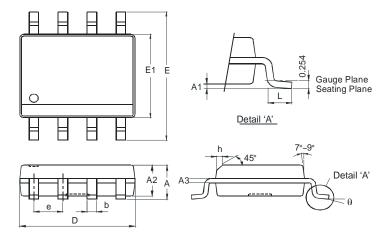
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



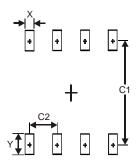


Package Outline Dimensions



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
E	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27



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